

# 74AHC245; 74AHCT245

Octal bus transceiver; 3-state

Rev. 05 — 28 April 2009

Product data sheet

## 1. General description

The 74AHC245; 74AHCT245 is a high-speed Si-gate CMOS device.

The 74AHC245; 74AHCT245 is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions.

The 74AHC245; 74AHCT245 features an output enable input ( $\overline{OE}$ ), for easy cascading, and a send and receive direction control input (DIR).

$\overline{OE}$  controls the outputs so that the buses are effectively isolated.

## 2. Features

- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than  $V_{CC}$
- Input levels:
  - ◆ For 74AHC245: CMOS level
  - ◆ For 74AHCT245: TTL level
- ESD protection:
  - ◆ HBM EIA/JESD22-A114E exceeds 2000 V
  - ◆ MM EIA/JESD22-A115-A exceeds 200 V
  - ◆ CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

## 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC245D 74AHCT245D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHC245PW 74AHCT245PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHC245BQ 74AHCT245BQ	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85$ mm	SOT764-1

## 4. Functional diagram

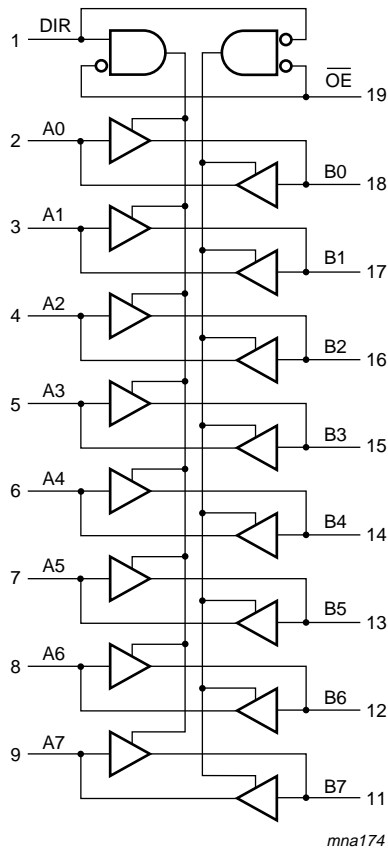


Fig 1. Logic symbol

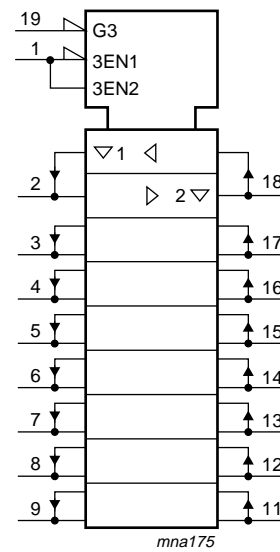
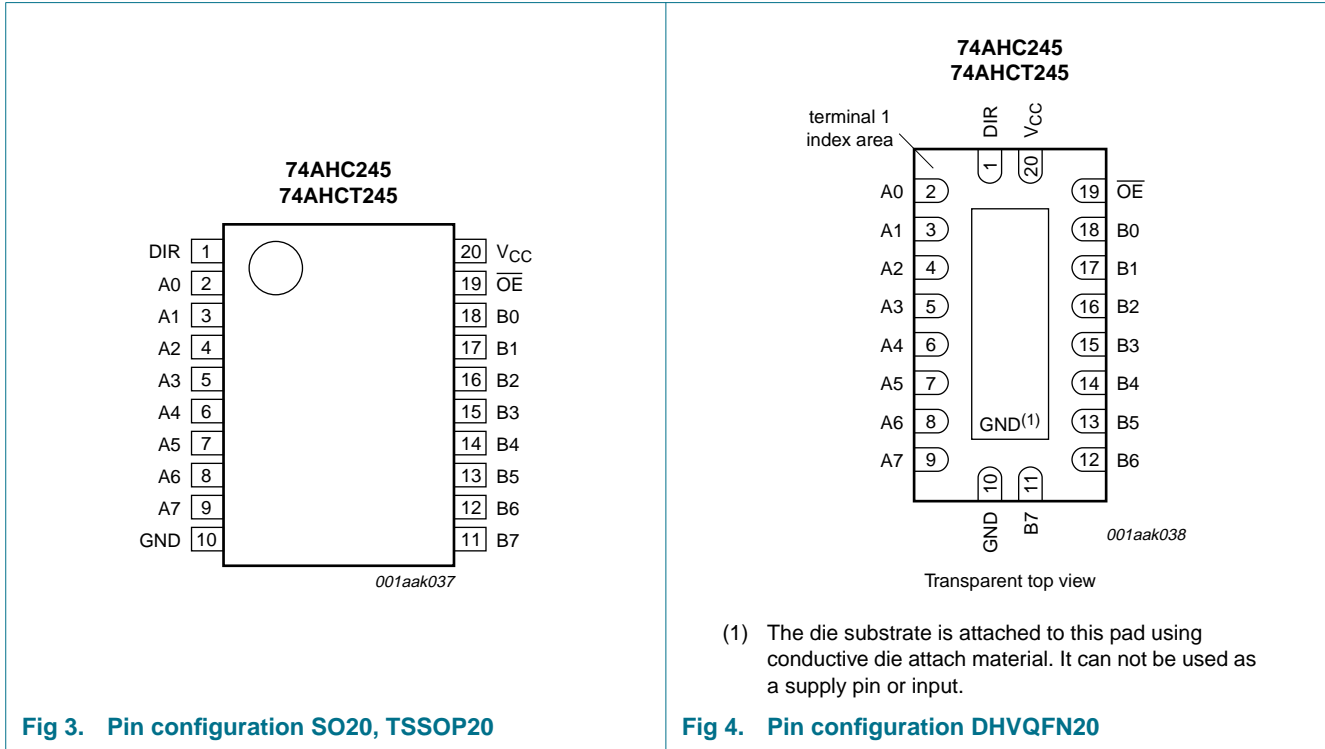


Fig 2. IEC logic symbol

## 5. Pinning information

### 5.1 Pinning



### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DIR	1	direction control input
A0	2	data input/output
A1	3	data input/output
A2	4	data input/output
A3	5	data input/output
A4	6	data input/output
A5	7	data input/output
A6	8	data input/output
A7	9	data input/output
GND	10	ground (0 V)
B7	11	data input/output
B6	12	data input/output
B5	13	data input/output
B4	14	data input/output
B3	15	data input/output
B2	16	data input/output

Table 2. Pin description ...continued

Symbol	Pin	Description
B1	17	data input/output
B0	18	data input/output
$\overline{\text{OE}}$	19	output enable input (active LOW)
$V_{\text{CC}}$	20	supply voltage

## 6. Functional description

Table 3. Function table<sup>[1]</sup>

Control		Input/output	
OE	DIR	An	Bn
L	L	A = B	inputs
L	H	inputs	B = A
H	X	Z	Z

- [1] H = HIGH voltage level;  
 L = LOW voltage level;  
 X = don't care;  
 Z = high-impedance OFF-state.

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{CC}}$	supply voltage		-0.5	+7.0	V
$V_{\text{I}}$	input voltage		-0.5	+7.0	V
$I_{\text{IK}}$	input clamping current	$V_{\text{I}} < -0.5 \text{ V}$	[1] -20	-	mA
$I_{\text{OK}}$	output clamping current	$V_{\text{O}} < -0.5 \text{ V}$ or $V_{\text{O}} > V_{\text{CC}} + 0.5 \text{ V}$	[1] -20	+20	mA
$I_{\text{O}}$	output current	$V_{\text{O}} = -0.5 \text{ V}$ to $(V_{\text{CC}} + 0.5 \text{ V})$	-25	+25	mA
$I_{\text{CC}}$	supply current		-	+75	mA
$I_{\text{GND}}$	ground current		-75	-	mA
$T_{\text{stg}}$	storage temperature		-65	+150	°C
$P_{\text{tot}}$	total power dissipation	$T_{\text{amb}} = -40 \text{ °C}$ to $+125 \text{ °C}$	[2] -	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.  
 [2] For SO20 packages: above 70 °C the value of  $P_{\text{tot}}$  derates linearly at 8 mW/K.  
 For TSSOP20 packages: above 60 °C the value of  $P_{\text{tot}}$  derates linearly at 5.5 mW/K.  
 For DHVQFN20 packages: above 60 °C the value of  $P_{\text{tot}}$  derates linearly at 4.5 mW/K.

## 8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>74AHC245</b>						
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	5.5	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	100	ns/V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	20	ns/V
<b>74AHCT245</b>						
V <sub>CC</sub>	supply voltage		4.5	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	5.5	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	20	ns/V

## 9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74AHC245</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V <sub>CC</sub> = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
	I <sub>O</sub> = -8.0 mA; V <sub>CC</sub> = 4.5 V	3.94	-	-	3.80	-	3.70	-	V	
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
	I <sub>O</sub> = 8.0 mA; V <sub>CC</sub> = 4.5 V	-	-	0.36	-	0.44	-	0.55	V	

**Table 6. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
$I_I$	input leakage current	$V_I = 5.5 \text{ V}$ or GND; $V_{CC} = 0 \text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	$\pm 0.25$	-	$\pm 2.5$	-	$\pm 10.0$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	$\mu\text{A}$
$C_I$	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
$C_O$	output capacitance		-	4	-	-	-	-	-	pF

**74AHCT245**

$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V}$ to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$ $I_O = -50 \mu\text{A}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$ $I_O = 50 \mu\text{A}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
$I_I$	input leakage current	$V_I = 5.5 \text{ V}$ or GND; $V_{CC} = 0 \text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND per input pin; other inputs at $V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	$\pm 0.25$	-	$\pm 2.5$	-	$\pm 10.0$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$ ; other pins at $V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
$C_I$	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
$C_O$	output capacitance		-	4	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	Min	Max	
<b>74AHC245</b>										
t <sub>pd</sub>	propagation delay	An to Bn; Bn to An; see Figure 5	[2]							
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	5.0	8.4	1.0	10.0	1.0	10.5	ns
		C <sub>L</sub> = 50 pF	-	6.5	11.9	1.0	13.5	1.0	15.0	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	3.5	5.5	1.0	6.5	1.0	7.0	ns
		C <sub>L</sub> = 50 pF		5.0	7.5	1.0	8.5	1.0	9.5	ns
t <sub>en</sub>	enable time	OE to An; OE to Bn; signal name DIR; see Figure 6	[3]							
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	6.5	13.2	1.0	15.5	1.0	16.5	ns
		C <sub>L</sub> = 50 pF	-	9.0	16.7	1.0	19.0	1.0	21.0	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	4.0	8.5	1.0	10.0	1.0	11.0	ns
		C <sub>L</sub> = 50 pF	-	5.0	10.6	1.0	12.0	1.0	13.5	ns
t <sub>dis</sub>	disable time	OE to An; OE to Bn; signal name DIR; see Figure 6	[4]							
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	7.5	12.5	1.0	15.5	1.0	16.0	ns
		C <sub>L</sub> = 50 pF	-	10.0	15.8	1.0	18.0	1.0	20.0	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	4.5	7.8	1.0	9.2	1.0	10.0	ns
		C <sub>L</sub> = 50 pF	-	6.0	9.7	1.0	11.0	1.0	12.5	ns
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; V <sub>i</sub> = GND to V <sub>CC</sub>	[5]	-	12	-	-	-	-	pF

74AHCT245; V<sub>CC</sub> = 4.5 V to 5.5 V

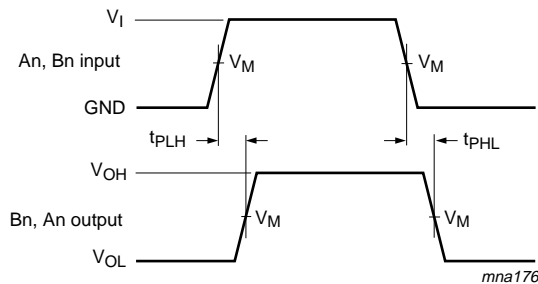
t <sub>pd</sub>	propagation delay	An to Bn; Bn to An; see Figure 5	[2]							
		C <sub>L</sub> = 15 pF	-	3.5	7.7	1.0	8.5	1.0	10.0	ns
		C <sub>L</sub> = 50 pF	-	4.5	8.7	1.0	9.5	1.0	11.0	ns
t <sub>en</sub>	enable time	OE to An; OE to Bn; signal name DIR; see Figure 6	[3]							
		C <sub>L</sub> = 15 pF	-	5.0	13.8	1.0	15.0	1.0	17.5	ns
		C <sub>L</sub> = 50 pF	-	6.0	14.8	1.0	16.0	1.0	18.5	ns

**Table 7. Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	Min	Max	
t <sub>dis</sub>	disable time	OE to An; OE to Bn; signal name DIR; see <a href="#">Figure 6</a>								
		C <sub>L</sub> = 15 pF	-	5.0	14.4	1.0	15.5	1.0	18.0	ns
		C <sub>L</sub> = 50 pF	-	6.0	15.4	1.0	16.5	1.0	19.5	ns
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; V <sub>i</sub> = GND to V <sub>CC</sub>	[5]	-	15	-	-	-	-	pF

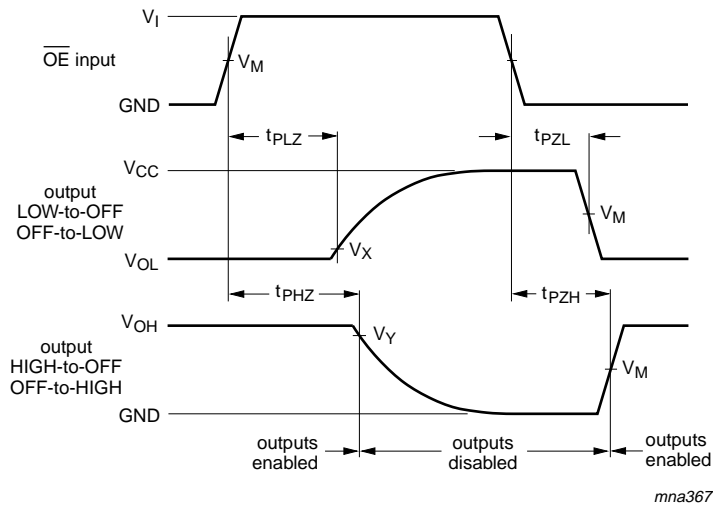
- [1] Typical values are measured at nominal supply voltage (V<sub>CC</sub> = 3.3 V and V<sub>CC</sub> = 5.0 V).
- [2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.
- [3] t<sub>en</sub> is the same as t<sub>PZL</sub> and t<sub>PZH</sub>.
- [4] t<sub>dis</sub> is the same as t<sub>PLZ</sub> and t<sub>PHZ</sub>.
- [5] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz;  
 f<sub>o</sub> = output frequency in MHz;  
 C<sub>L</sub> = output load capacitance in pF;  
 V<sub>CC</sub> = supply voltage in V;  
 N = number of inputs switching;  
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

### 10.1 Waveforms



Measurement points are given in [Table 8](#).  
 V<sub>OL</sub> and V<sub>OH</sub> are typical voltage output levels that occur with the output load.

**Fig 5. Input to output propagation delays**

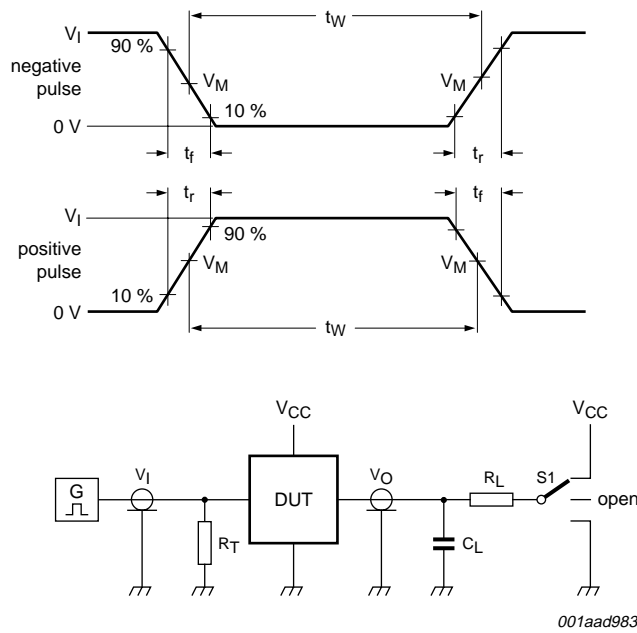


Measurement points are given in [Table 8](#).  
 $V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 6. Enable and disable times**

**Table 8. Measurement points**

Type	Input	Output		
	$V_M$	$V_M$	$V_X$	$V_Y$
74AHC245	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$
74AHCT245	1.5 V	$0.5 \times V_{CC}$	$V_{OL} + 0.3 \text{ V}$	$V_{OH} - 0.3 \text{ V}$



Test data is given in [Table 9](#).

Definitions test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_L$  = Load resistance.

S1 = Test selection switch.

**Fig 7. Load circuitry for measuring switching times**

**Table 9. Test data**

Type	Input		Load		S1 position		
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
74AHC245	$V_{CC}$	$\leq 3.0$ ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$
74AHCT245	3.0 V	$\leq 3.0$ ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$

11. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

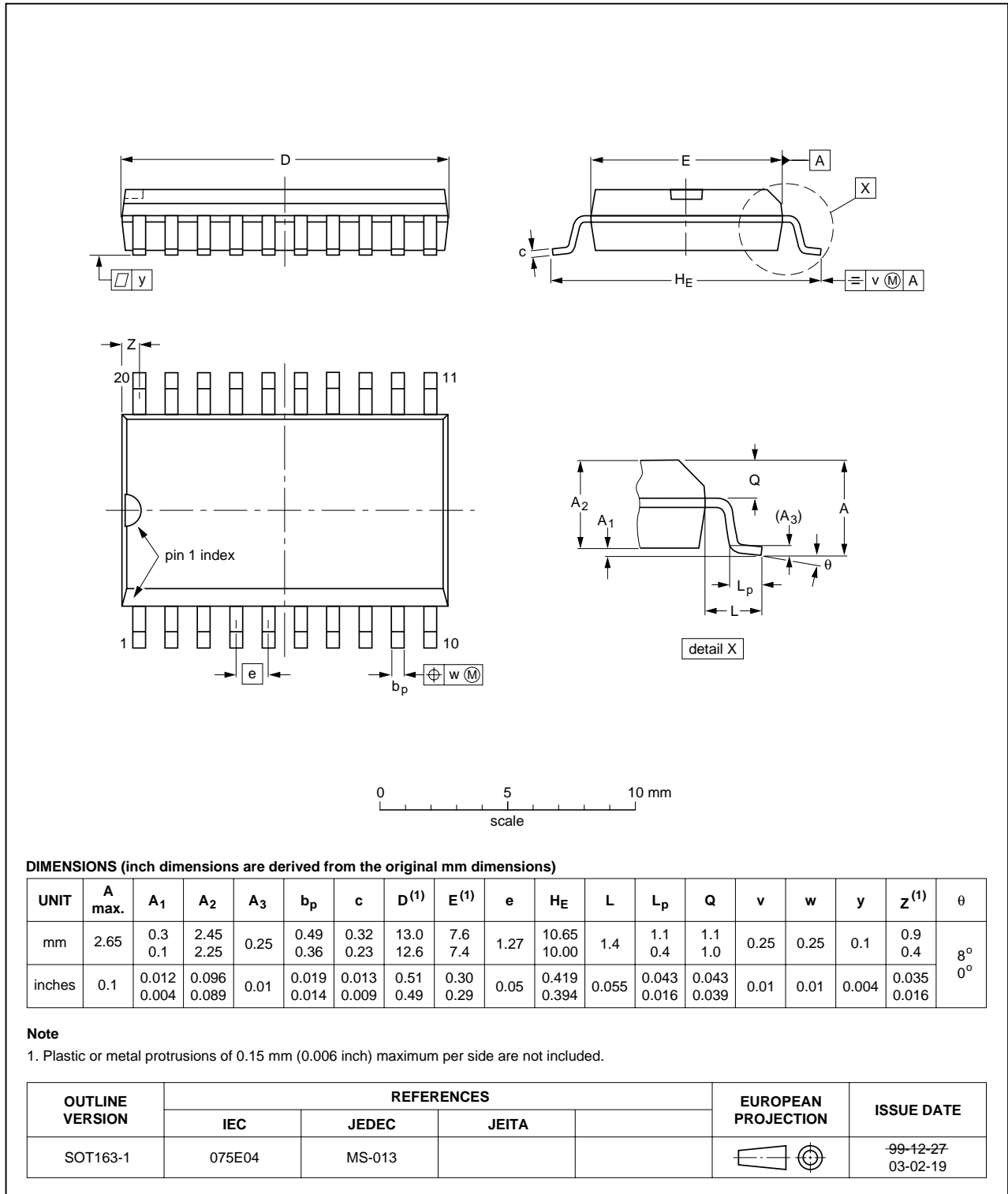


Fig 8. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

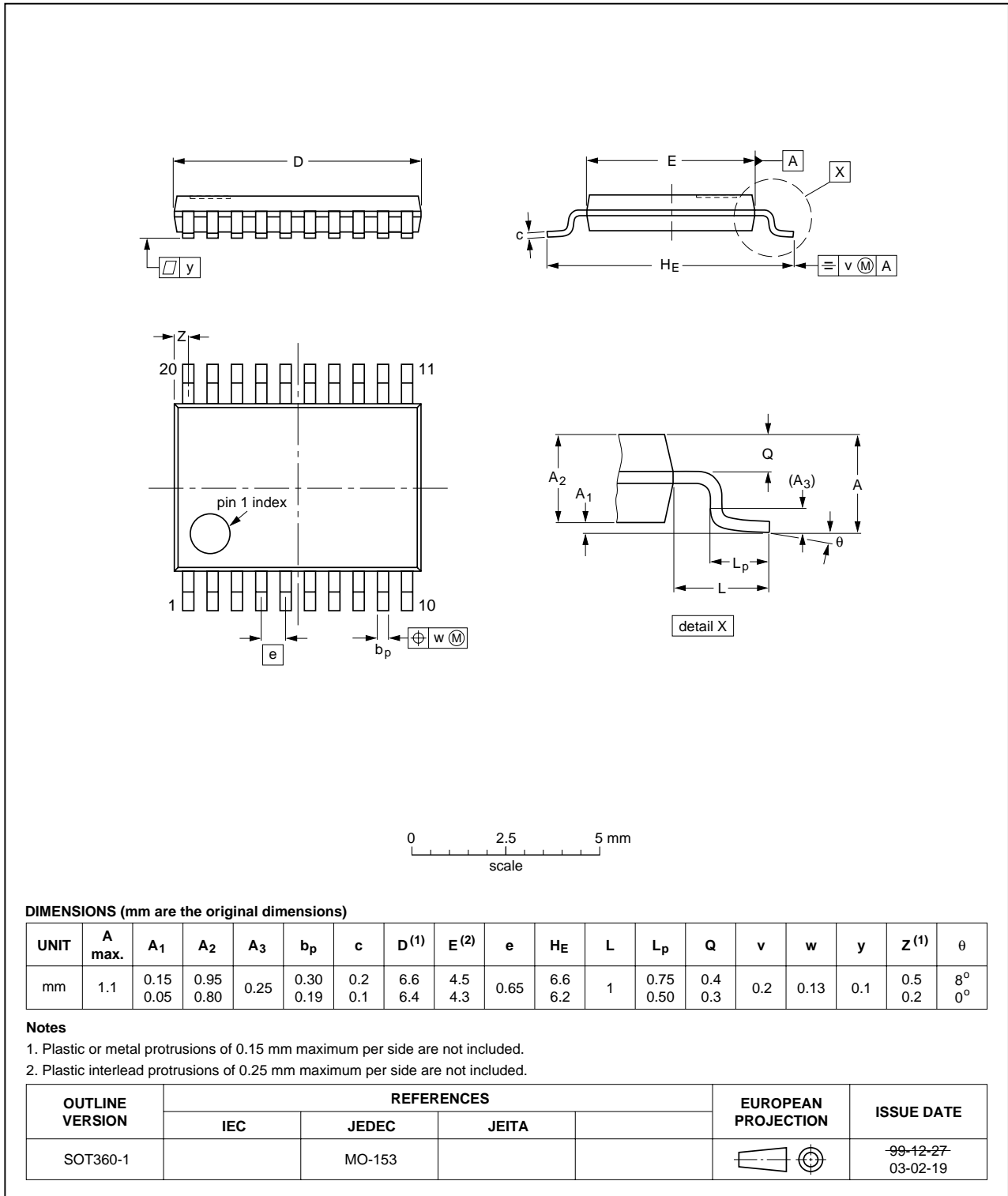
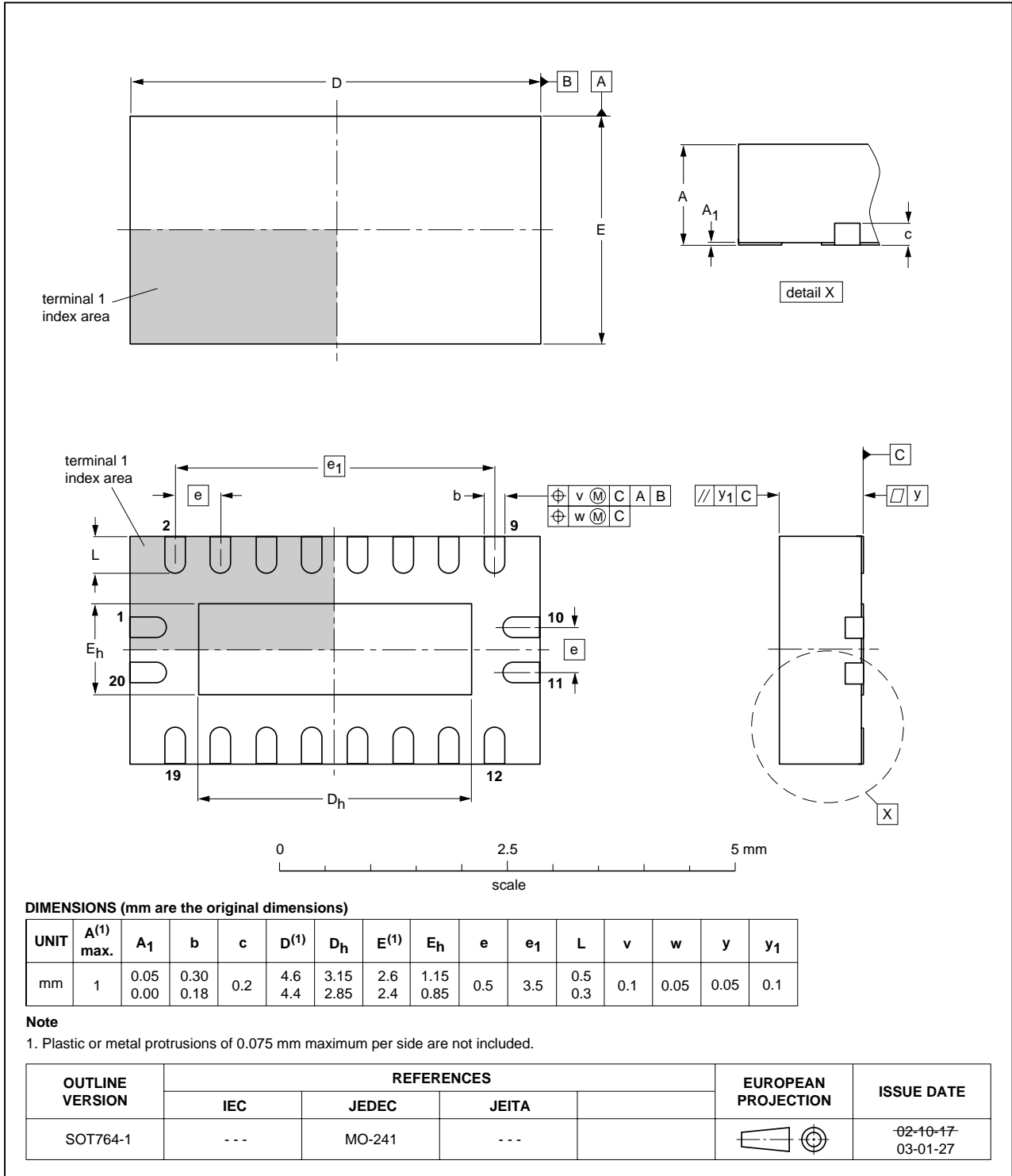


Fig 9. Package outline SOT360-1 (TSSOP20)

**DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm**

**SOT764-1**



**Fig 10. Package outline SOT764-1 (DHVQFN20)**

## 12. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 13. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT245_5	20090428	Product data sheet	-	74AHC_AHCT245_4
Modifications:		<ul style="list-style-type: none"> <li>• <a href="#">Section 3</a>: DHVQFN20 package added.</li> <li>• <a href="#">Section 7</a>: derating values added for DHVQFN20 package.</li> <li>• <a href="#">Section 11</a>: outline drawing added for DHVQFN20 package.</li> </ul>		
74AHC_AHCT245_4	20080425	Product data sheet	-	74AHC_AHCT245_N_3
74AHC_AHCT245_N_3	20070925	Product data sheet	-	74AHC_AHCT245_2
74AHC_AHCT245_2	19990928	Product specification	-	74AHC_AHCT245_1
74AHC_AHCT245_1	19980921	Product specification	-	-

## 14. Legal information

### 14.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 14.2 Definitions

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